

BCW65ALT1G, BCW65CLT1G

General Purpose Transistor

NPN Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	32	Vdc
Collector – Base Voltage	V_{CBO}	60	Vdc
Emitter – Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1), $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

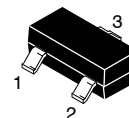
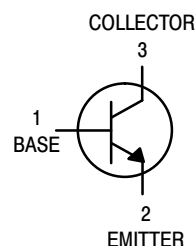
1. FR–5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



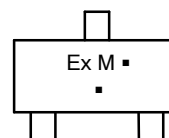
ON Semiconductor®

<http://onsemi.com>



SOT–23
CASE 318
STYLE 6

MARKING DIAGRAMS



Ex = Device Code
x = A or C
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BCW65ALT1G	SOT–23 (Pb–Free)	3000/Tape & Reel
BCW65CLT1G	SOT–23 (Pb–Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BCW65ALT1G, BCW65CLT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	32	–	–	Vdc
Collector–Emitter Breakdown Voltage (I _C = 10 μAdc, V _{EB} = 0)	V _{(BR)CES}	60	–	–	Vdc
Emitter–Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	–	–	Vdc
Collector Cutoff Current (V _{CE} = 32 Vdc, I _E = 0) (V _{CE} = 32 Vdc, I _E = 0, T _A = 150°C)	I _{CES}	– –	– –	20 20	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	–	–	20	nAdc

ON CHARACTERISTICS

DC Current Gain (I _C = 100 μAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 1.0 Vdc) (I _C = 100 mAdc, V _{CE} = 1.0 Vdc) (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)	BCW65ALT1	h _{FE}	35 75 100 35	– – – –	– – 250 –	–
DC Current Gain (I _C = 100 μAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 1.0 Vdc) (I _C = 100 mAdc, V _{CE} = 1.0 Vdc) (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)	BCW65CLT1	h _{FE}	80 180 250 100	– – – –	– – 630 –	–
Collector–Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc) (I _C = 100 mAdc, I _B = 10 mAdc)		V _{CE(sat)}	– –	0.7 0.3	– –	Vdc
Base–Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc)		V _{BE(sat)}	–	–	2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I _C = 20 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	100	–	–	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	–	–	12	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	–	–	80	pF
Noise Figure (V _{CE} = 5.0 Vdc, I _C = 0.2 mAdc, R _S = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

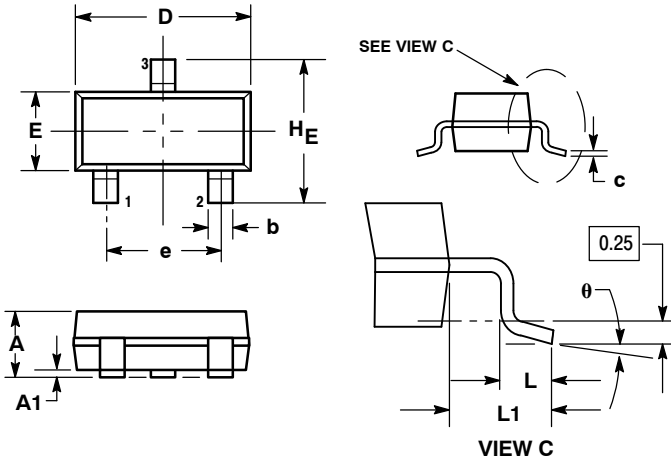
SWITCHING CHARACTERISTICS

Turn–On Time (I _{B1} = I _{B2} = 15 mAdc)	t _{on}	–	–	100	ns
Turn–Off Time (I _C = 150 mAdc, R _L = 150 Ω)	t _{off}	–	–	400	ns

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PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN



NOTES:

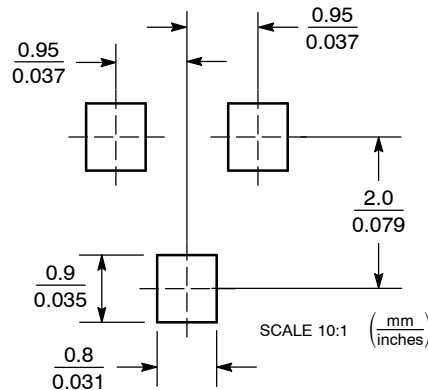
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H _E	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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